

13. Device (1; 100) according to any one of the preceding claims, characterized in that the first nozzle (18; 152), the second nozzles (18; 142) and the additional nozzle (156) are arranged in a common base (10; 120).
- 5 14. Device (1; 100) according to any one of the preceding claims, characterized by an insert (35) that is provided with the first nozzle (38), and which is insertable into the base (10).
- 10 15. Device (1; 100) according to any one of the preceding claims, characterized in that the second nozzles (18; 142; 144) are formed in a nozzle plate (17; 140) of the base (10; 120).
- 15 16. Device (1; 100) according to any one of the preceding claims, characterized by a ring-shaped fluid chamber (22; 146) beneath the nozzle plate (17; 140).
- 20 17. Device (1; 100) according to any one of the preceding claims, characterized by a surface of the base (10) with a plurality of bores surrounding the nozzle plate (17; 140) and lying deeper relative to this nozzle plate and having a corresponding number of spacers (13).
18. Device (1; 100) according to claim 17, characterized in that the spacers (13) are adjustable.

19. Device (1; 100) according to any one of the preceding claims, characterized by an overflow collar (50) on the base (10).
20. Device (1; 100) according to claim 19, characterized by at least one inwardly directed nozzle (55) on the overflow collar (50);
21. Device (1; 100) according to any one of the preceding claims, characterized by a tank surrounding the base (10).
22. Device (1; 100) according to any one of the preceding claims, characterized by a unit (108) for conducting a fluid onto an outer side of a substrate carrier (103) holding a substrate therein.
23. Device (1; 100) according to claim 22, characterized in that the unit (108) is arranged on the substrate carrier (103).
24. Method for processing substrates (2), in particular semiconductor wafers, having the following steps:
 - conducting a fluid at a right angle onto a surface of the substrate (2) to be treated via at least one first nozzle (38; 152) arranged substantially concentrically relative to the substrate, so that the fluid strikes the substrate in a radial flow; and

- conducting a fluid onto the surface of the substrate (2) to be treated via a plurality of second nozzles (18; 142) separately controllable relative to the first nozzle and transverse to the radial flow.

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25. Method according to claim 24, characterized in that the fluid is conducted via the second nozzles (18; 142; 144) in essentially the peripheral direction of the substrate (2) onto the surface to be treated.

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26. Method according to claim 24 or 25, characterized in that the fluid is conducted via the second nozzles (18; 142; 144) at an angle of 45° onto the surface of the substrate (2) to be treated.

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27. Method according to any one of claims 24 through 26, characterized in that the fluid is conducted onto the surface of the substrate (2) to be treated with different pressures via the first and second nozzles.

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28. Method according to any one of claims 24 through 27, characterized in that different fluids are conducted via the first and second nozzles onto the surface of the substrate (2) to be treated.

29. Method according to any one of claims 24 through 38, characterized in that a rinsing fluid is conducted via the